Vincotech

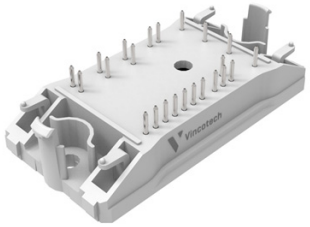
10-FZ12PMA005M701-P848A288
datasheet

flowPIM 0 **1200 V / 5 A**

Features

- IGBT M7 with low VCEsat and improved EMC behavior
- Open emitter configuration
- Compact and low inductive design
- Builtin NTC

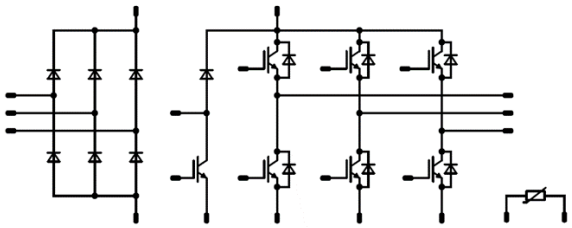
flow 0 housing



Target applications

- Industrial Drives

Schematic



Types

- 10-FZ12PMA005M701-P848A288

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C		5	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	10	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	41	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V Vcc = 800 V T_j = 150°C	9,5	µs
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F		5	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}	10	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	24	W
Maximum junction temperature	T_{jmax}		175	°C
Brake Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C		5	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	10	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	41	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V Vcc = 800 V T_j = 150°C	9,5	µs
Maximum junction temperature	T_{jmax}		175	°C
Brake Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F		5	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}	10	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	24	W
Maximum junction temperature	T_{jmax}		175	°C
Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F		35	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 150 °C	270	A
Surge current capability	I^2t		370	A^2s
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	56	W
Maximum junction temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
		AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance			9,29	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$		10		0,0005	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		5	25 125 150		1,62 1,83 1,89	1,95	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			20	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		1100		pF
Output capacitance	C_{oes}							57		
Reverse transfer capacitance	C_{res}							11		
Gate charge	Q_g		15	600	5	25		40		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,30		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 64 Ω R_{goff} = 64 Ω	±15	600	5	25 125 150		153 149 147		ns
Rise time	t_r					25 125 150		39 43 43		
Turn-off delay time	$t_{d(off)}$					25 125 150		154 176 181		
Fall time	t_f					25 125 150		89 115 111		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 0,6 µC Q_{rFWD} = 0,9 µC Q_{rFWD} = 1 µC				25 125 150		0,480 0,601 0,643		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,333 0,440 0,473		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				5	25 125 150		1,57 1,65 1,65	2,1	V
Reverse leakage current	I_R			1200		25			20	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						3,50		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 83 A/µs di/dt = 99 A/µs di/dt = 92 A/µs	±15	600	5	25 125 150		4 4 4		A
Reverse recovery time	t_{rr}					25 125 150		259 387 434		ns
Recovered charge	Q_r					25 125 150		0,551 0,873 0,985		µC
Reverse recovered energy	E_{rec}					25 125 150		0,186 0,330 0,378		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		46 25 25		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$		10		0,0005	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		5	25 125 150		1,62 1,83 1,89	1,95	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			20	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		1100		pF
Output capacitance	C_{oes}							57		
Reverse transfer capacitance	C_{res}							11		
Gate charge	Q_g		15	600	5	25		40		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,30		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 64 Ω R_{gon} = 64 Ω	15/0	600	5	25 125 150		79 73 72		ns
Rise time	t_r					25 125 150		45 48 49		
Turn-off delay time	$t_{d(off)}$					25 125 150		234 262 270		
Fall time	t_f					25 125 150		101 114 117		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 0,6 µC Q_{rFWD} = 0,8 µC Q_{rFWD} = 0,9 µC				25 125 150		0,480 0,609 0,634		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,345 0,454 0,474		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				5	25 125 150		1,57 1,65 1,65	2,1	V
Reverse leakage current	I_R			1200		25			20	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						3,50		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 85 A/µs di/dt = 102 A/µs di/dt = 87 A/µs	15/0	600	5	25 125 150		4 4 4		A
Reverse recovery time	t_{rr}					25 125 150		259 386 431		ns
Recovered charge	Q_r					25 125 150		0,558 0,833 0,935		µC
Reverse recovered energy	E_{rec}					25 125 150		0,200 0,314 0,363		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		37 24 20		A/µs
Rectifier Diode										
Static										
Forward voltage	V_F				35	25 125		1,17 1,13		V
Reverse leakage current	I_R			1600		25			50	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,25		K/W

Characteristic Values

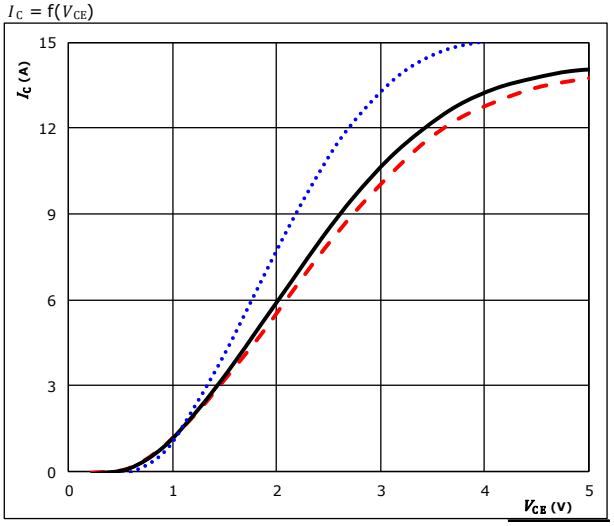
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		5		mW
Power dissipation constant						25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %				25		3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %				25		4000		K
Vincotech NTC Reference									I	

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

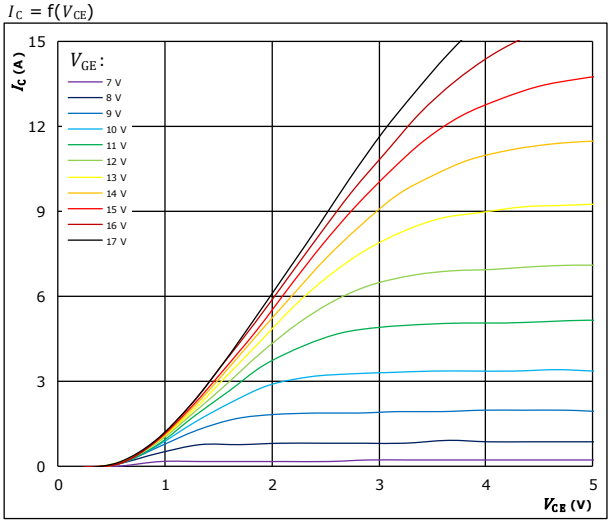


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

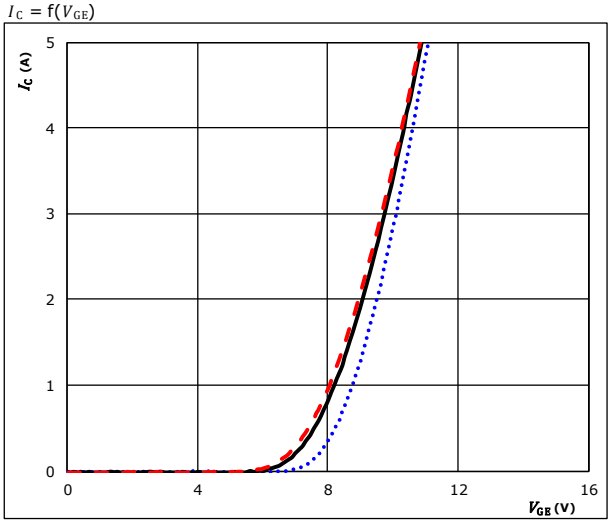


t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

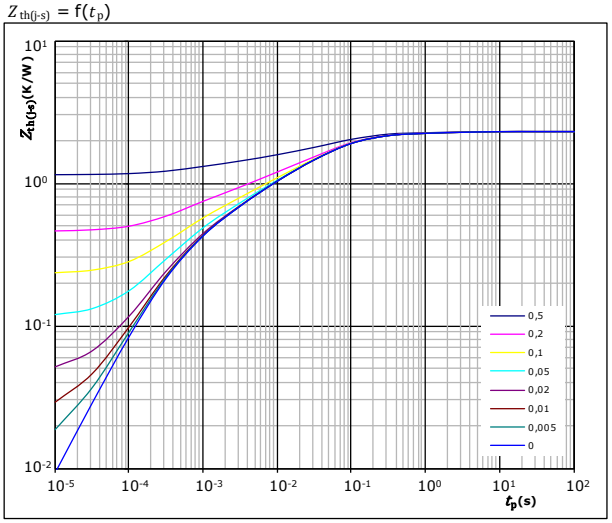


t_p =	100	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	2,30	K/W

IGBT thermal model values

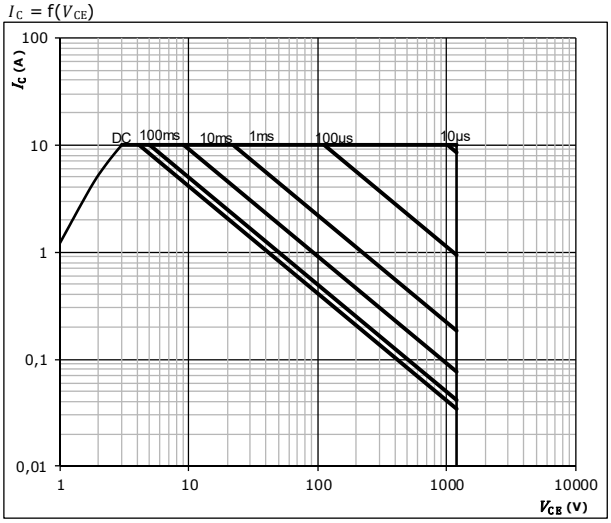
R (K/W)	τ (s)
6,25E-02	3,48E+00
1,37E-01	5,00E-01
7,38E-01	8,11E-02
5,28E-01	2,49E-02
3,84E-01	5,54E-03
2,39E-01	1,24E-03
2,13E-01	3,29E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



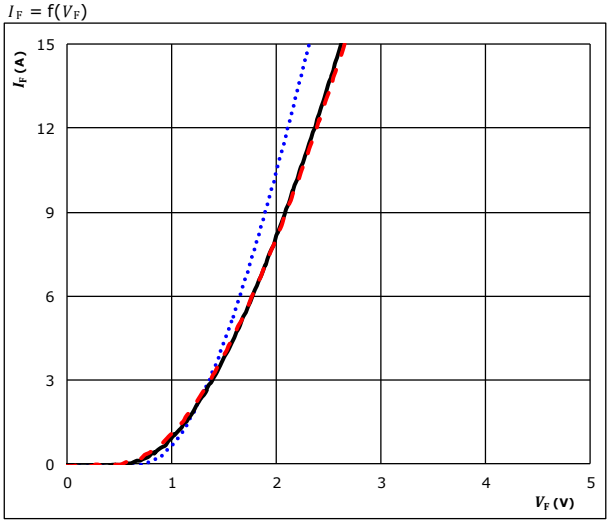
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



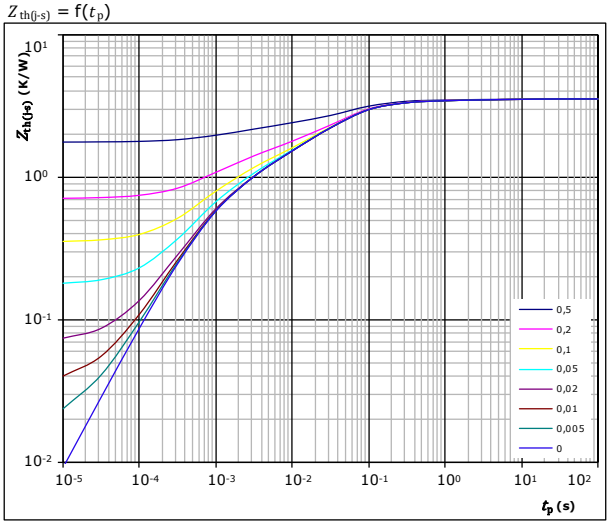
t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 3,50 K/W

FWD thermal model values

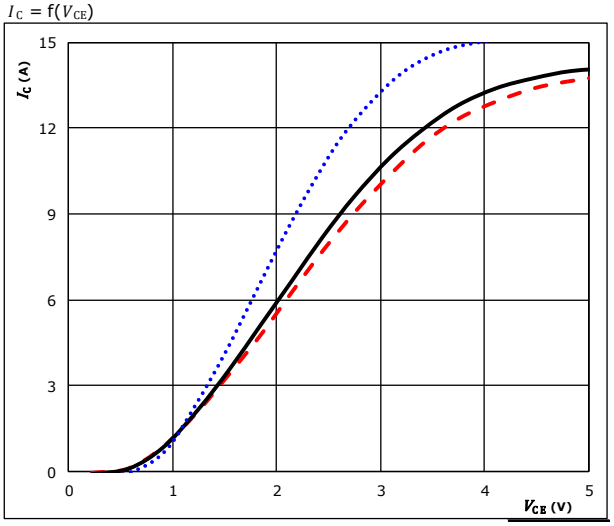
R (K/W)	τ (s)
8,03E-02	7,23E+00
2,34E-01	4,70E-01
1,33E+00	6,36E-02
7,92E-01	2,24E-02
5,71E-01	3,34E-03
4,85E-01	7,05E-04

Brake Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

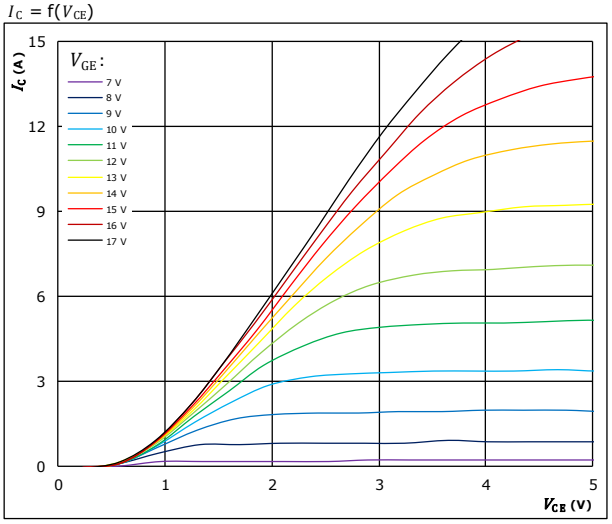


t_p =	250	µs		25 °C	·····
V_{GE} =	15	V	T_j:	125 °C	———
				150 °C	– – –

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

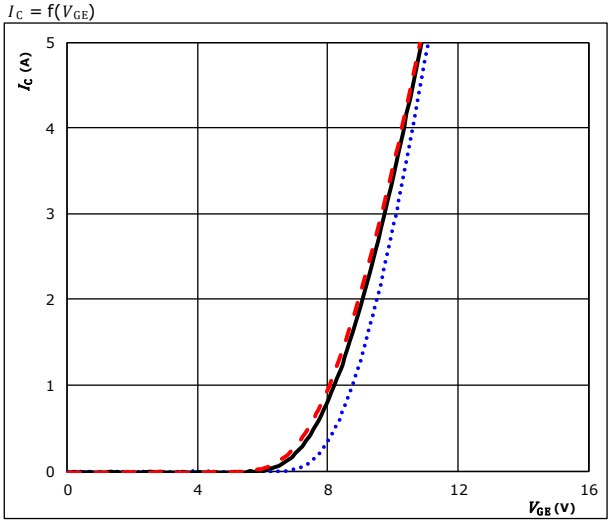


t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

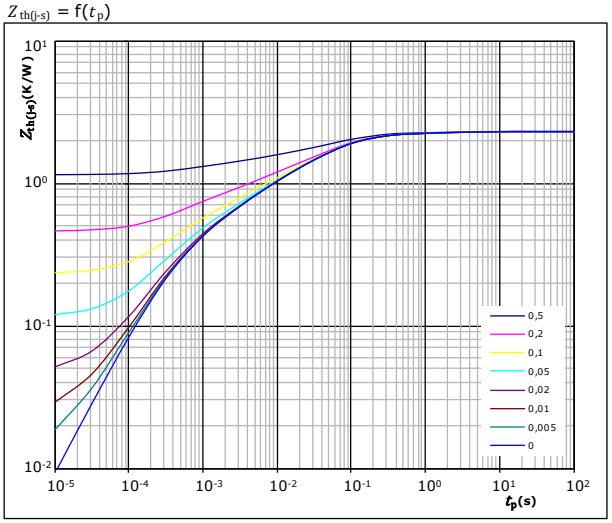


t_p =	100	µs		25 °C	·····
V_{CE} =	10	V	T_j:	125 °C	———
				150 °C	– – –

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	2,30	K/W

IGBT thermal model values

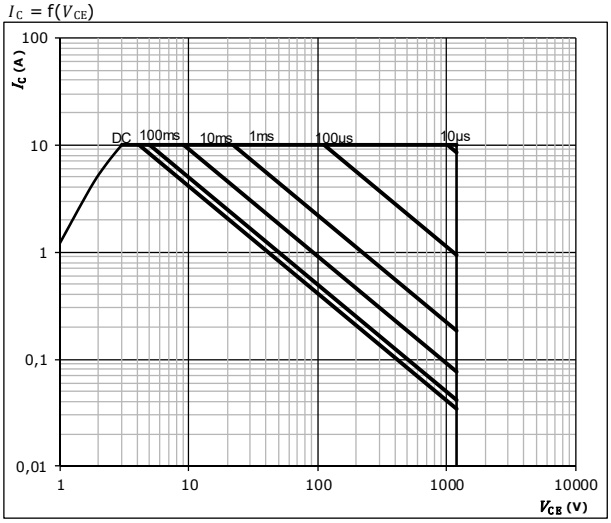
R (K/W)	τ (s)
6,25E-02	3,48E+00
1,37E-01	5,00E-01
7,38E-01	8,11E-02
5,28E-01	2,49E-02
3,84E-01	5,54E-03
2,39E-01	1,24E-03
2,13E-01	3,29E-04

Brake Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



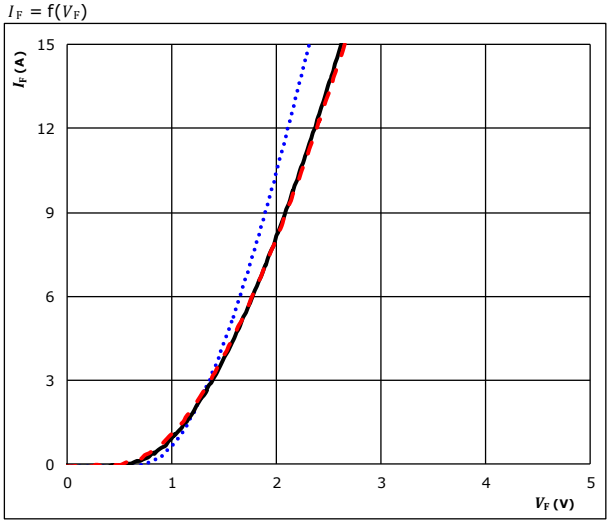
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Brake Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



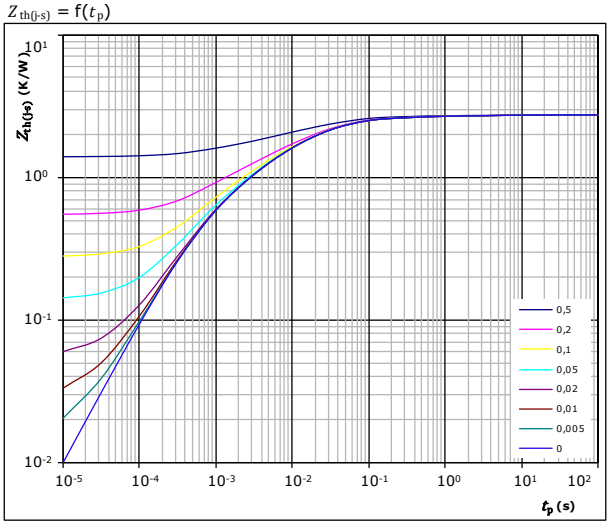
t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,76 K/W

FWD thermal model values

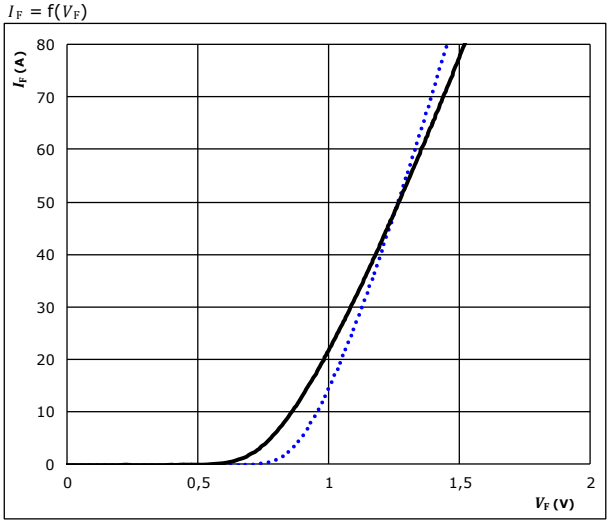
R (K/W)	τ (s)
6,58E-02	4,81E+00
1,43E-01	3,47E-01
6,08E-01	4,61E-02
8,65E-01	1,40E-02
7,08E-01	2,91E-03
3,69E-01	5,42E-04

Rectifier Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



t_p = 250 µs

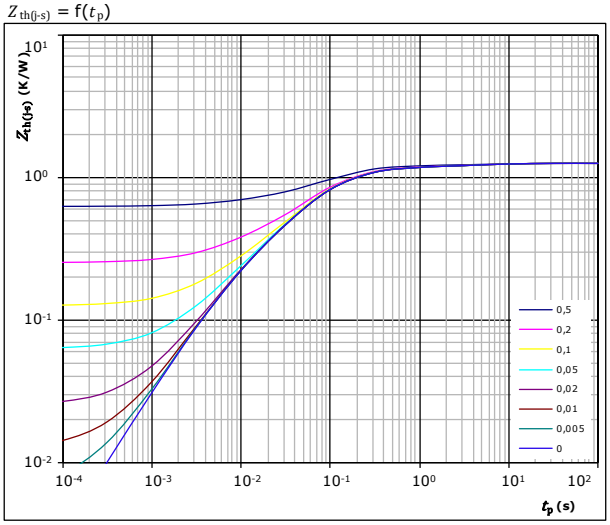
T_j: 25 °C

125 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,25 K/W

FWD thermal model values

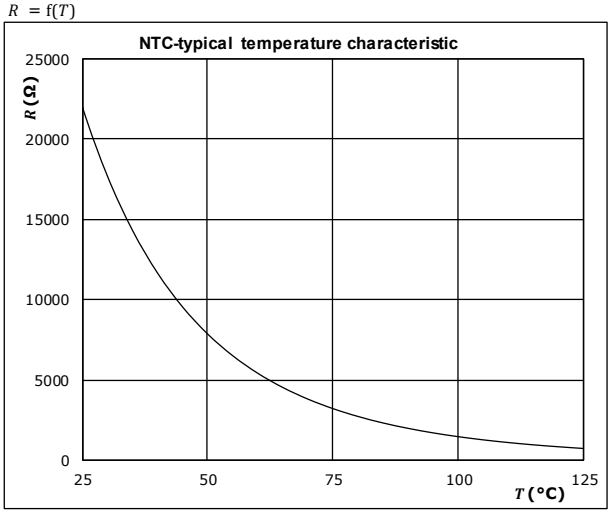
R (K/W)	τ (s)
8,00E-02	5,22E+00
1,56E-01	4,18E-01
6,95E-01	8,82E-02
2,23E-01	3,07E-02
9,97E-02	5,99E-03

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic as a function of temperature

$R = f(T)$

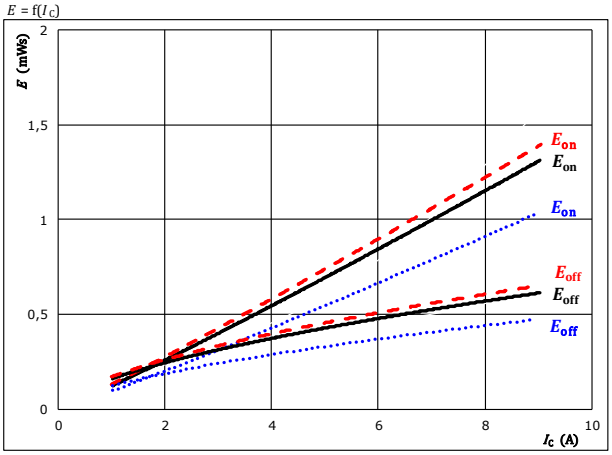


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



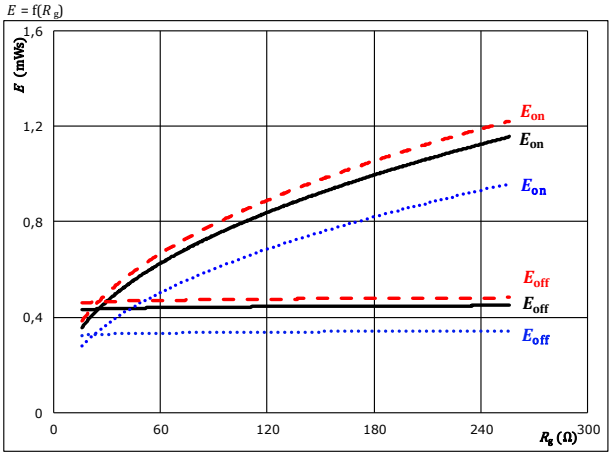
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	64	Ω		150 °C
R_{goff} =	64	Ω		

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



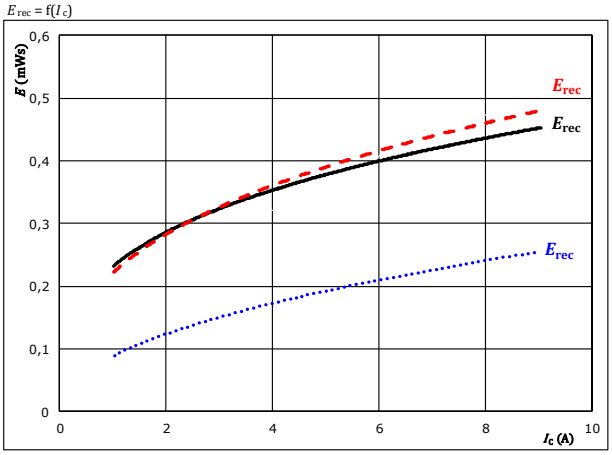
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	5	A		150 °C

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_c)$



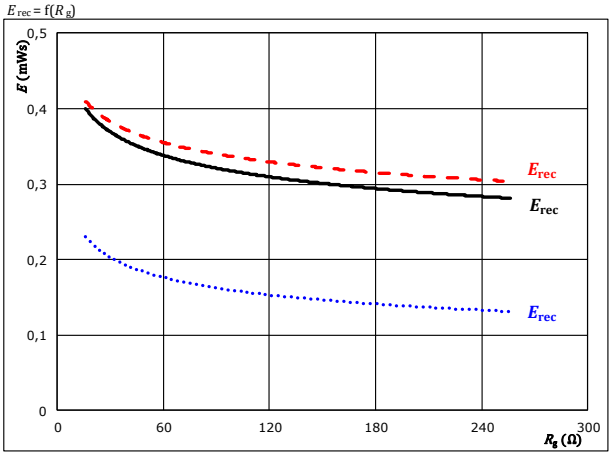
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	64	Ω		150 °C

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

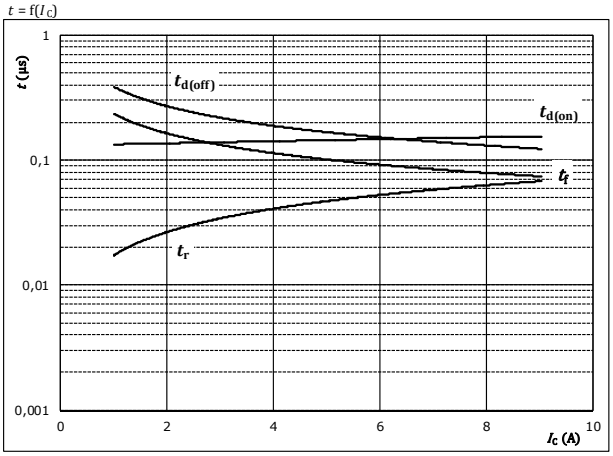
V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	5	A		150 °C

Inverter Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



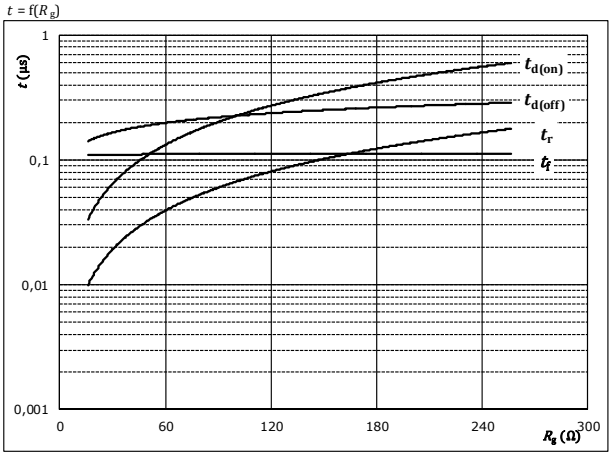
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	64	Ω
R_{goff} =	64	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



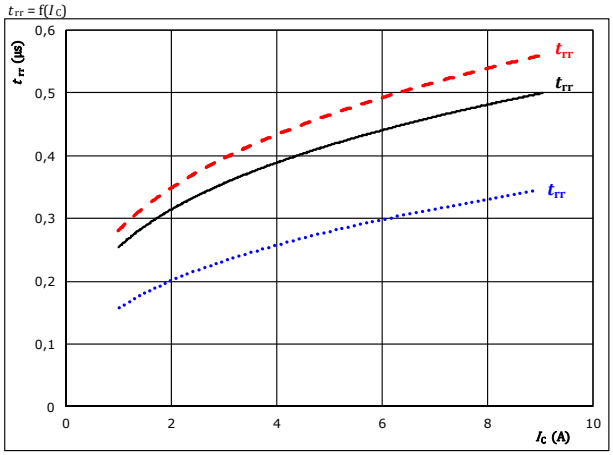
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	5	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

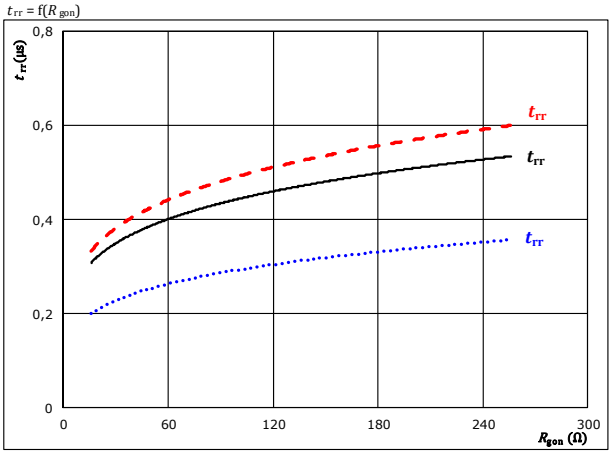
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	5	A

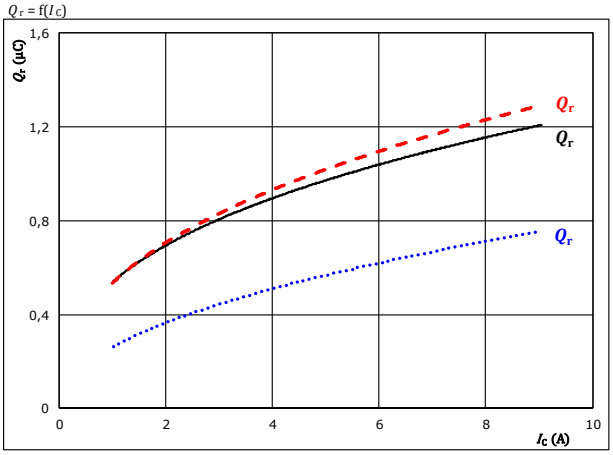
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$



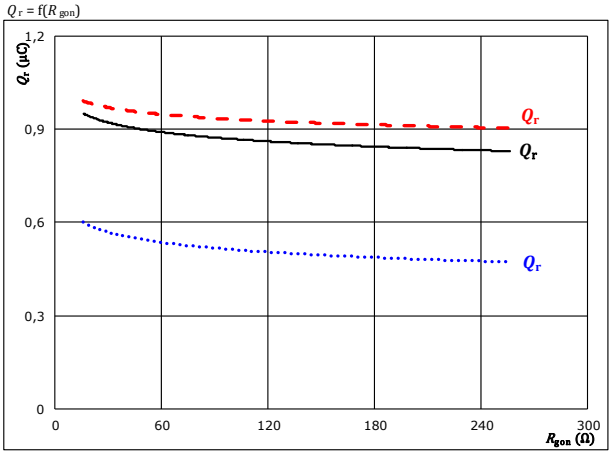
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	64	Ω		150 °C	

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$



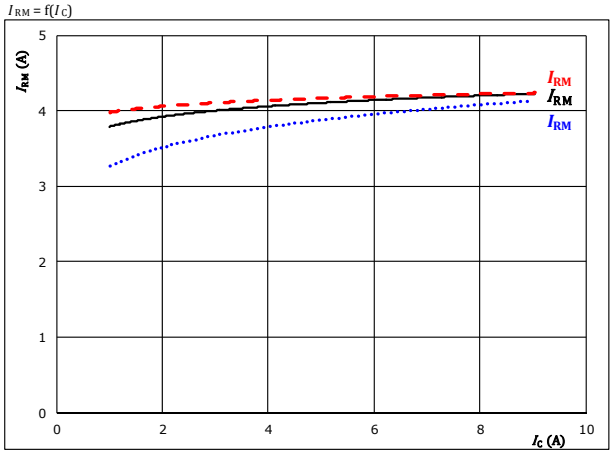
With an inductive load at

V_{CE}=	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C=	5	A		150 °C	

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$



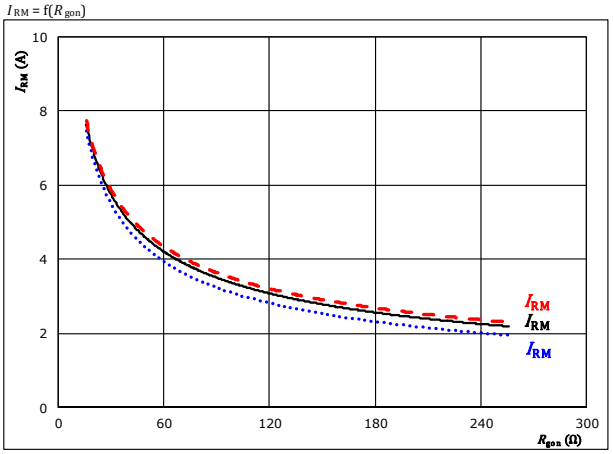
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	64	Ω		150 °C	

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

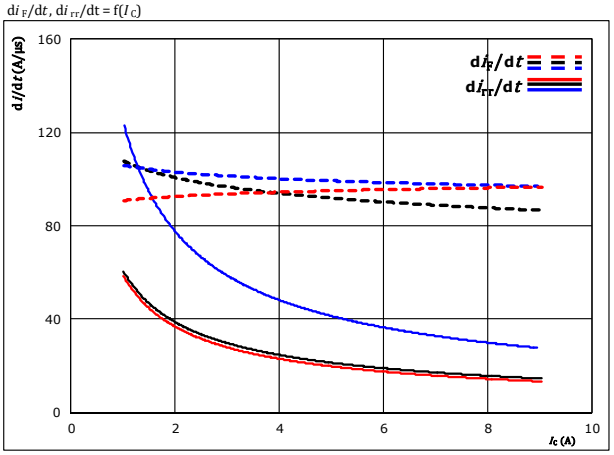
V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C =	5	A		150 °C	

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, $di_{rr}/dt = f(I_C)$



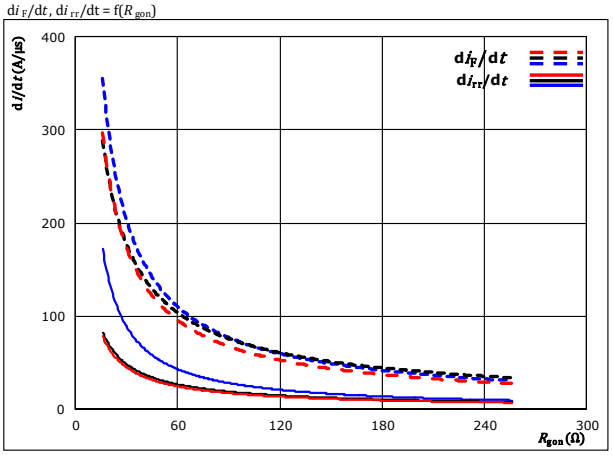
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	64	Ω		150 °C

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, $di_{rr}/dt = f(R_{gon})$



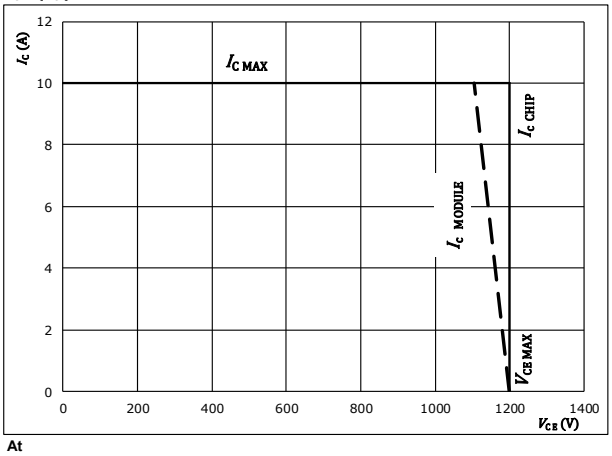
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C=	5	A		150 °C

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	125	°C
R_{gon} =	64	Ω
R_{goff} =	64	Ω

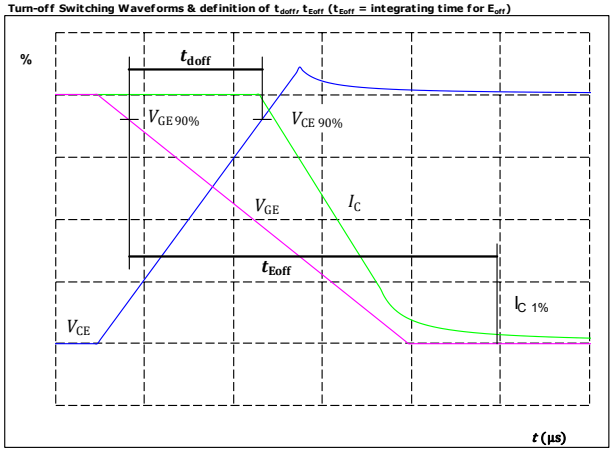
Inverter Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	64 Ω
R_{goff}	=	64 Ω

figure 1. IGBT

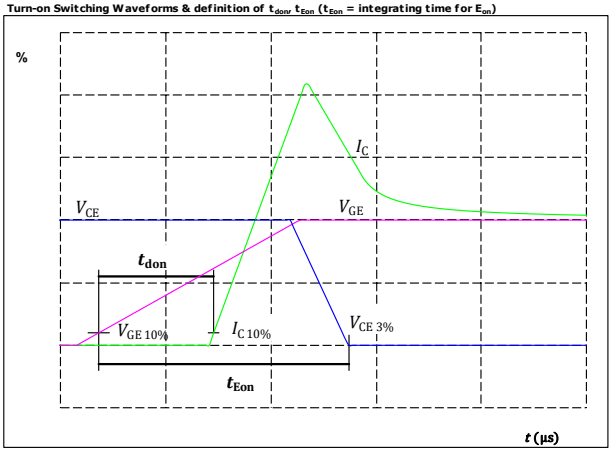
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_{doff} =	176	ns

figure 2. IGBT

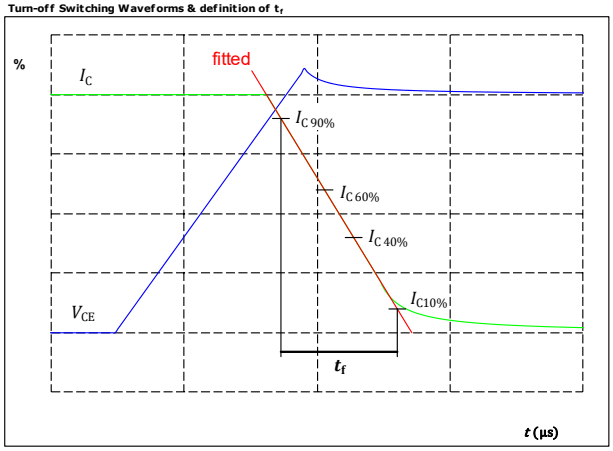
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_{don} =	149	ns

figure 3. IGBT

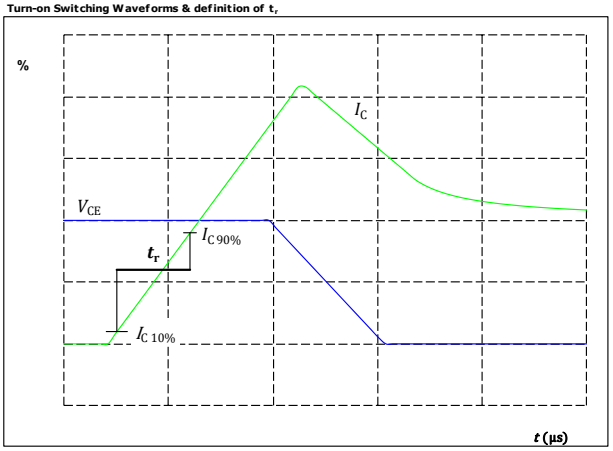
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_f =	115	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

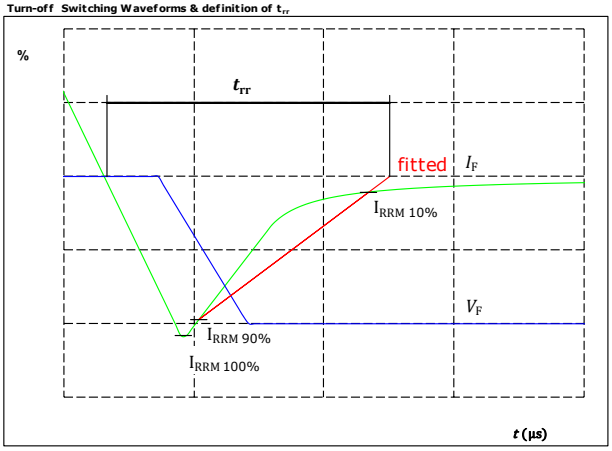


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_r =	43	ns

Inverter Switching Definitions

figure 5. **FWD**

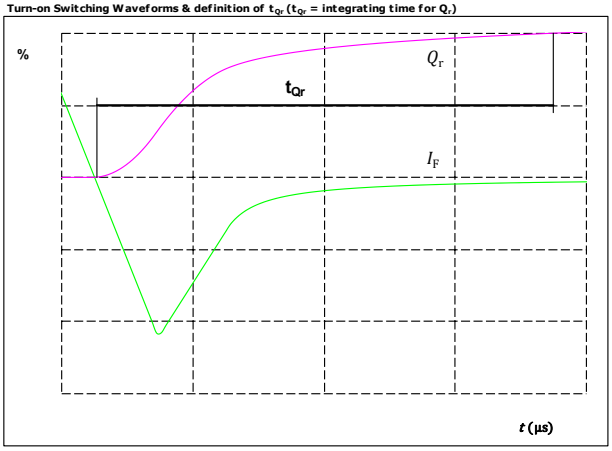
Turn-off Switching Waveforms & definition of t_{rr}



$V_F(100\%) =$	600	V
$I_F(100\%) =$	5	A
$I_{RRM}(100\%) =$	4	A
$t_{rr} =$	387	ns

figure 6. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



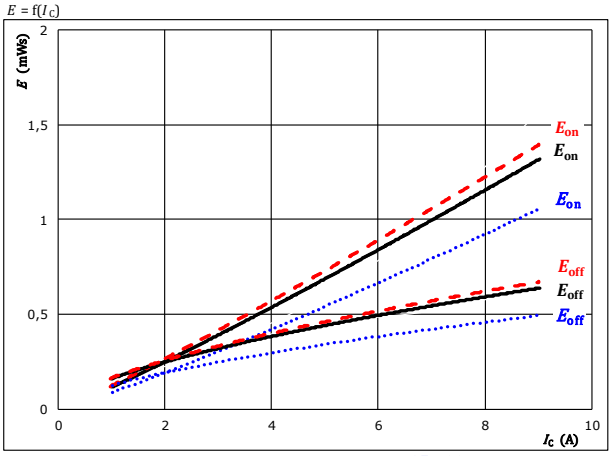
$I_F(100\%) =$	5	A
$Q_r(100\%) =$	0,87	µC

Brake Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



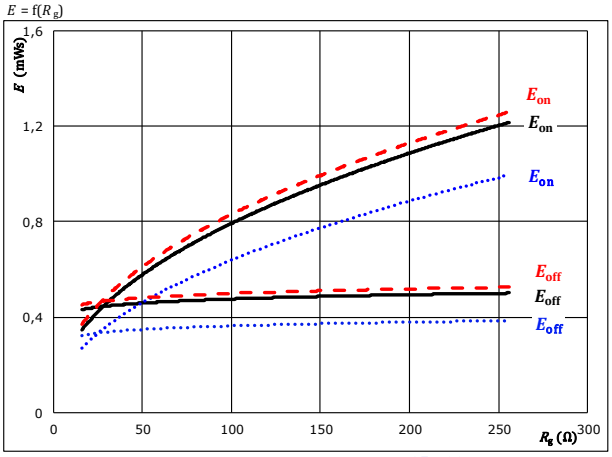
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	·····
V_{GE} =	15/0	V		125 °C	———
R_{gon} =	64	Ω		150 °C	– – –
R_{goff} =	64	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



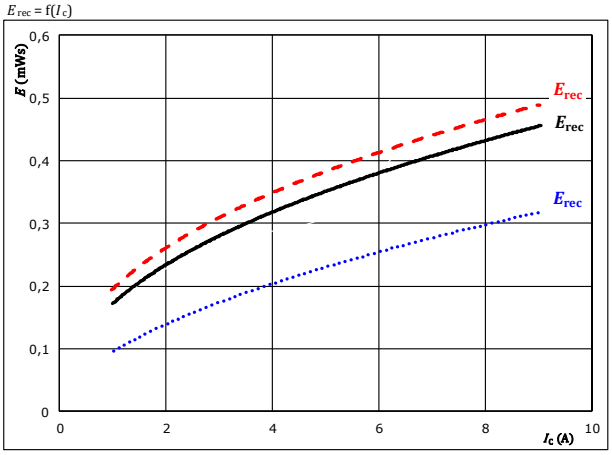
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	·····
V_{GE} =	15/0	V		125 °C	———
I_C =	5	A		150 °C	– – –

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



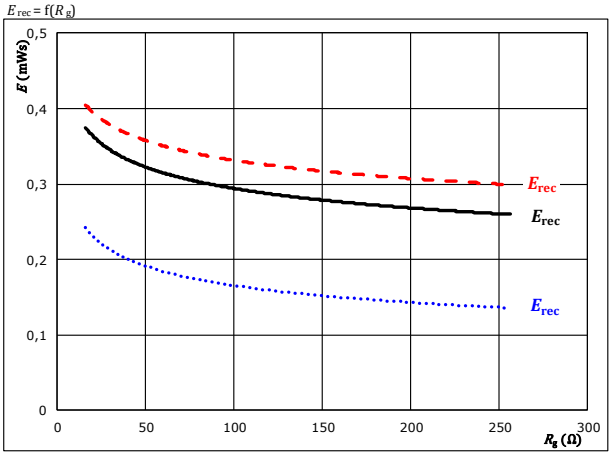
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	·····
V_{GE} =	15/0	V		125 °C	———
R_{gon} =	64	Ω		150 °C	– – –

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

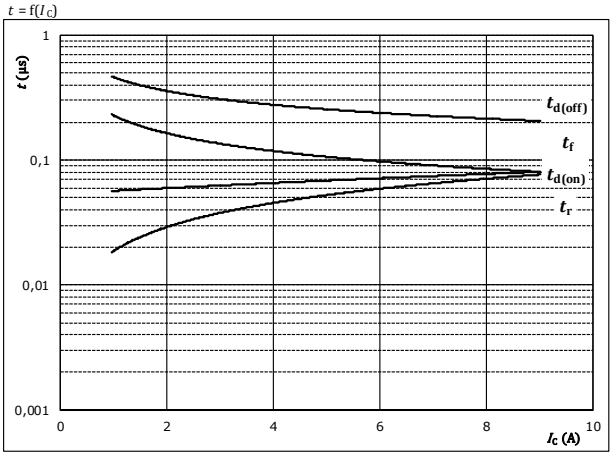
V_{CE} =	600	V	T_j:	25 °C	·····
V_{GE} =	15/0	V		125 °C	———
I_C =	5	A		150 °C	– – –

Brake Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



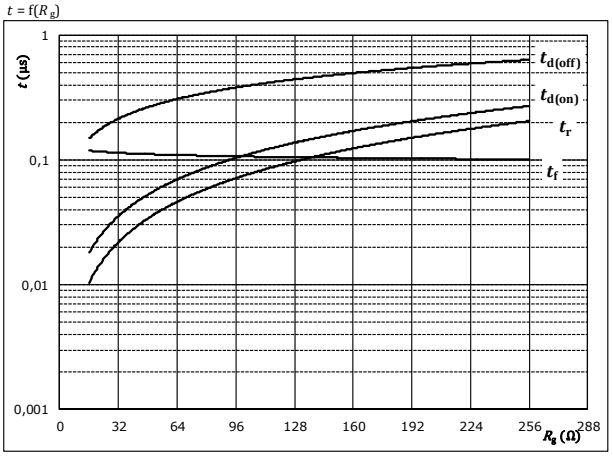
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	15/0	V
R_{gon} =	64	Ω
R_{goff} =	64	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



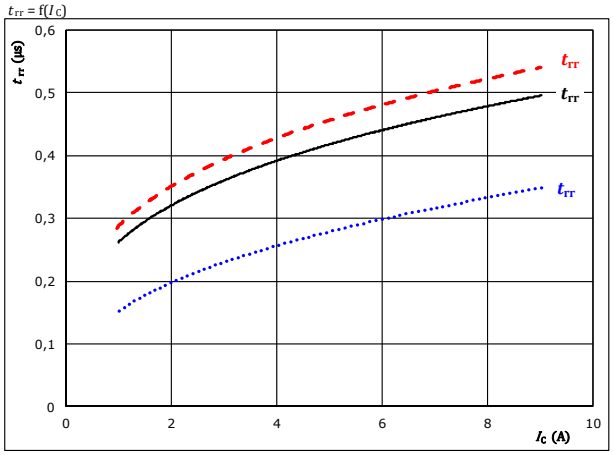
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	15/0	V
I_C =	5	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

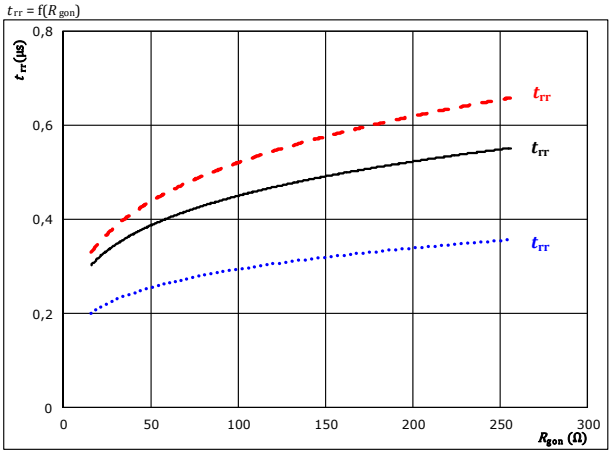


At					
	V_{CE} =	600	V		25 °C
	V_{GE} =	15/0	V	T_j:	125 °C
	R_{gon} =	64	Ω		150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



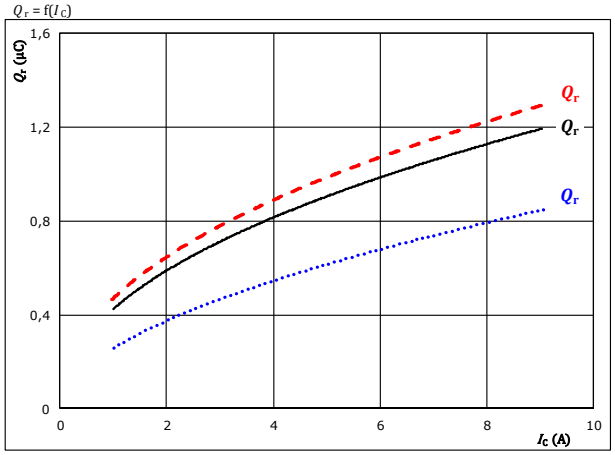
At					
	V_{CE} =	600	V		25 °C
	V_{GE} =	15/0	V	T_j:	125 °C
	I_C =	5	A		150 °C

Brake Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

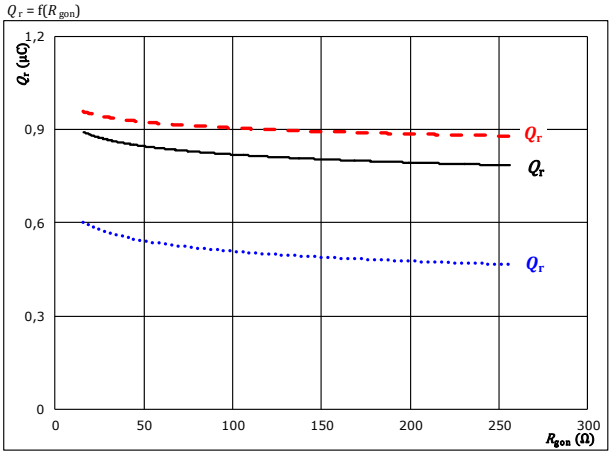


At						
	V_{CE} =	600	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	R_{gon} =	64	Ω		150 °C	

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

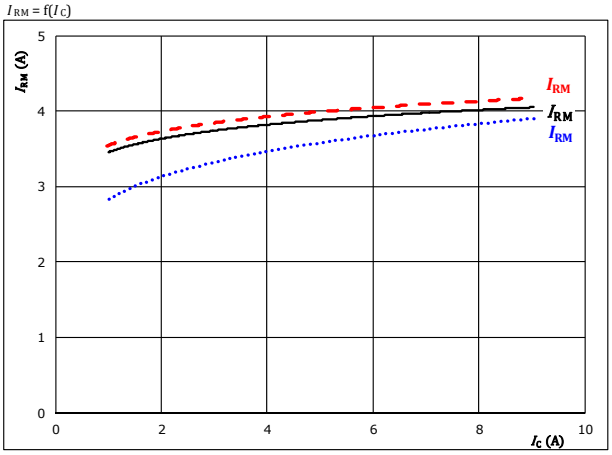


At						
	V_{CE}=	600	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	I_C=	5	A		150 °C	

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

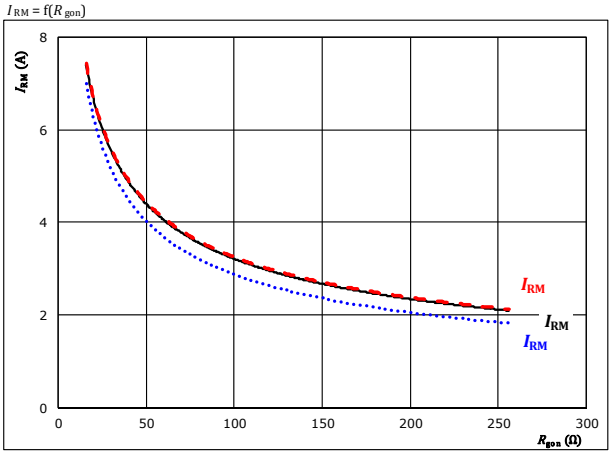


At						
	V_{CE}:	600	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	R_{gon} =	64	Ω		150 °C	

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



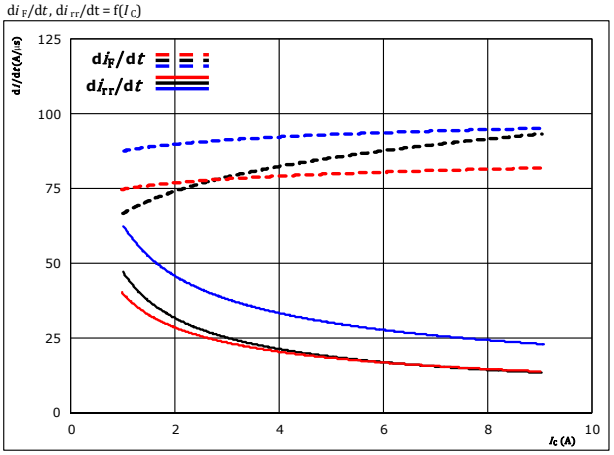
At						
	V_{CE} =	600	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	I_C =	5	A		150 °C	

Brake Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt, di_{rr}/dt = f(I_C)$

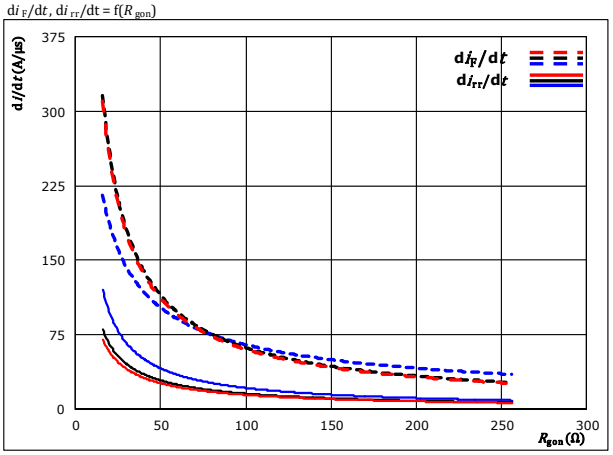


At					
V_{CE} =	600	V		25 °C	
V_{GE} =	15/0	V	T_j:	125 °C	
R_{gon} =	64	Ω		150 °C	

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_{gon})$

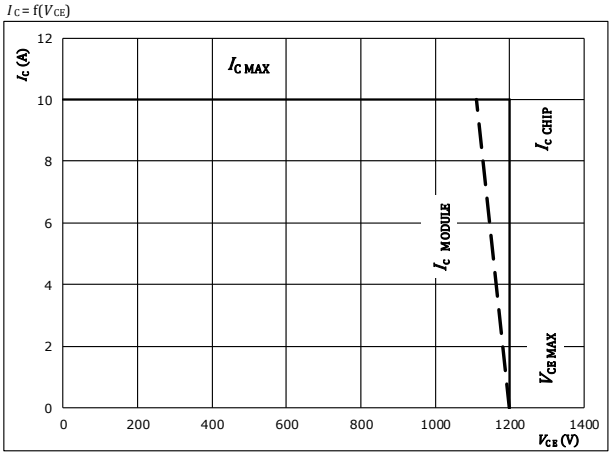


At					
V_{CE} =	600	V		25 °C	
V_{GE} =	15/0	V	T_j:	125 °C	
I_C =	5	A		150 °C	

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	175	°C
R_{gon} =	64	Ω
R_{goff} =	64	Ω

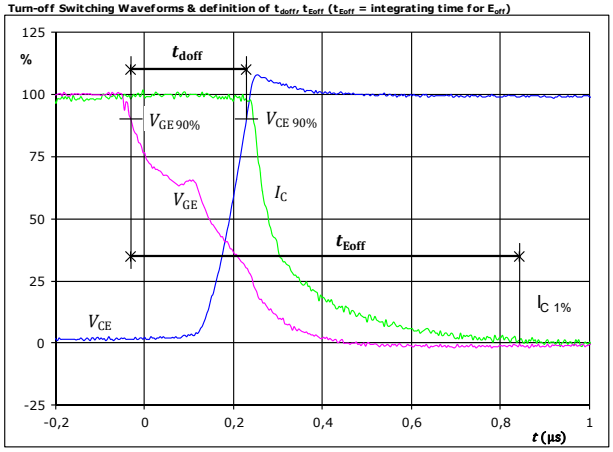
Brake Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	64 Ω
R_{goff}	=	64 Ω

figure 1. IGBT

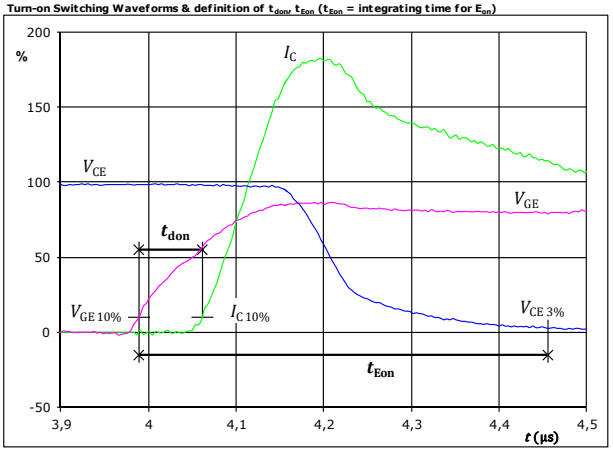
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_{doff} =	0,262	µs
t_{Eoff} =	0,874	µs

figure 2. IGBT

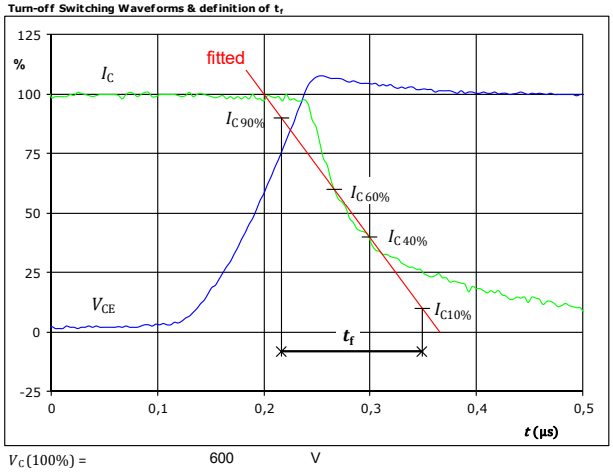
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_{don} =	0,073	µs
t_{Eon} =	0,467	µs

figure 3. IGBT

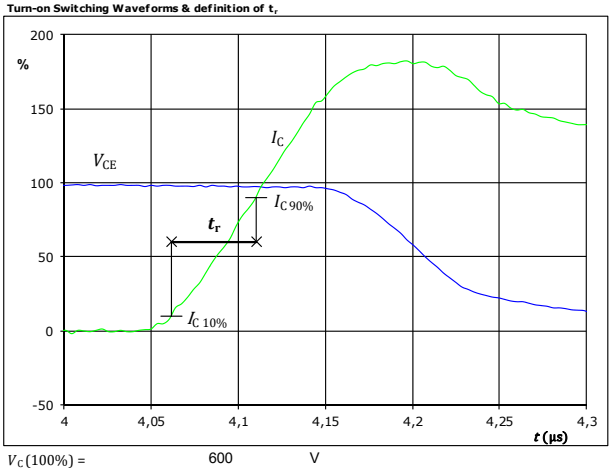
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_f =	0,114	µs

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

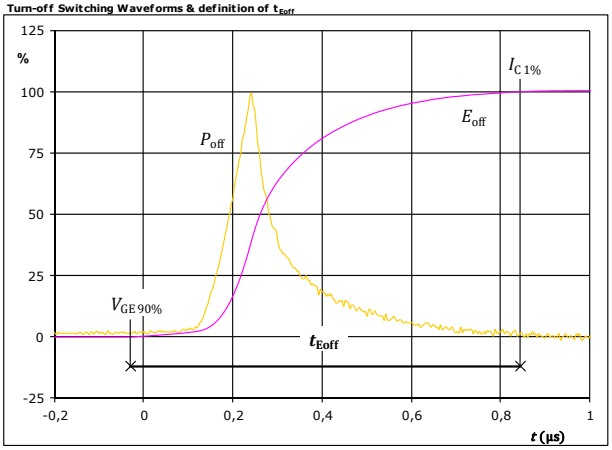


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	5	A
t_r =	0,048	µs

Brake Switching Characteristics

figure 5. **IGBT**

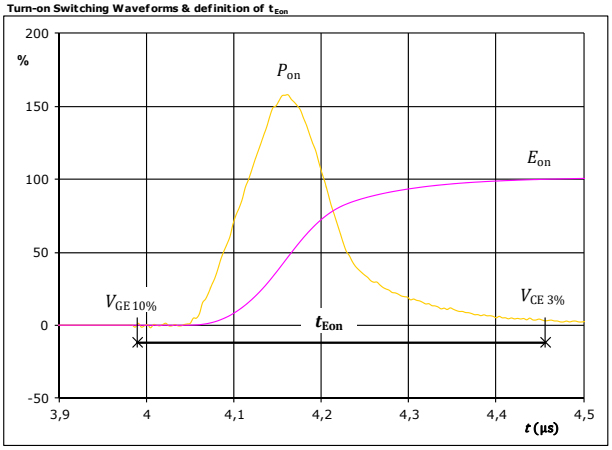
Turn-off Switching Waveforms & definition of t_{Eoff}



$P_{off}(100\%)$ =	3,03	kW
$E_{off}(100\%)$ =	0,45	mJ
t_{Eoff} =	0,87	µs

figure 6. **IGBT**

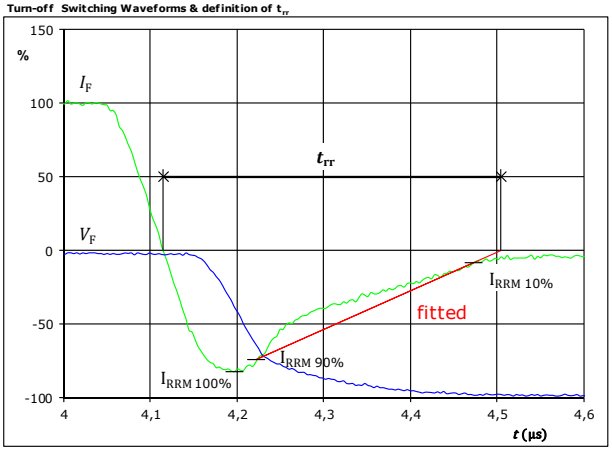
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on}(100\%)$ =	3,03	kW
$E_{on}(100\%)$ =	0,61	mJ
t_{Eon} =	0,47	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

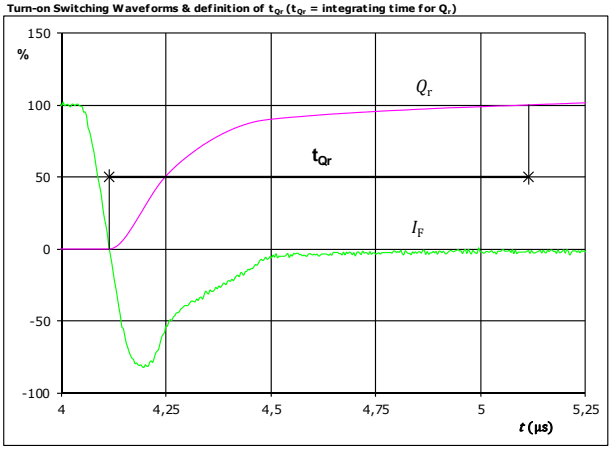


$V_F(100\%)$ =	600	V
$I_F(100\%)$ =	5	A
$I_{RRM}(100\%)$ =	-4	A
t_{rr} =	0,386	µs

Switching Characteristics

figure 8. **FWD**

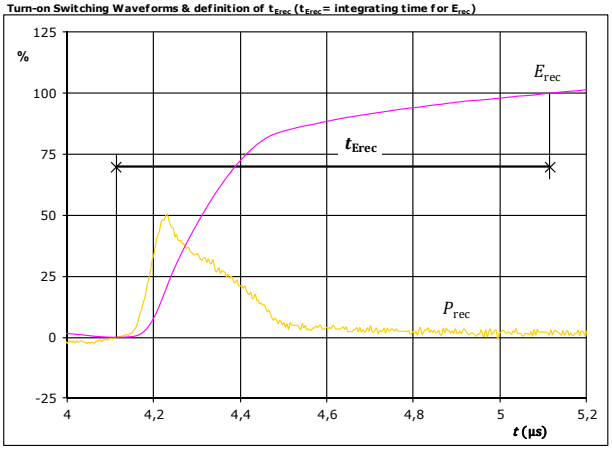
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	5	A
Q_r (100%) =	0,83	µC
t_{Qr} =	1,00	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



P_{rec} (100%) =	3,03	kW
E_{rec} (100%) =	0,31	mJ
t_{Erec} =	1,00	µs

Vincotech

Ordering Code & Marking

Version	Ordering Code
without thermal paste	10-FZ12PMA005M701-P848A288

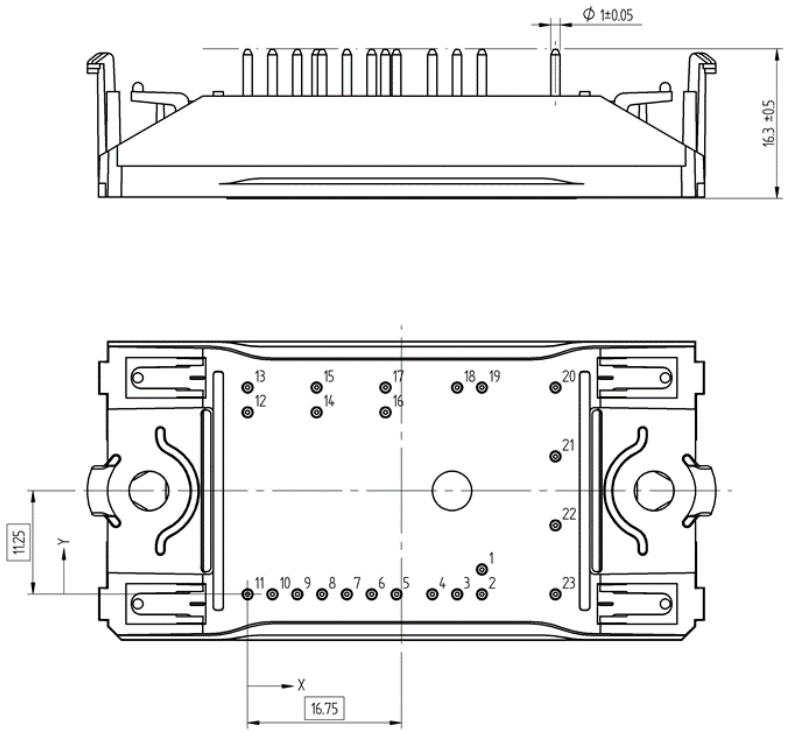
NN-NNNNNNNNNNNNNN
TTTTTTVV WWYY UL
VIN LLLLL SSSS

	Name	Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV	WWYY	UL VIN	LLLLL	SSSS

	Type&Ver	Lot number	Serial	Date code		
Datamatrix	TTTTTTVV	LLLLL	SSSS	WWYY		

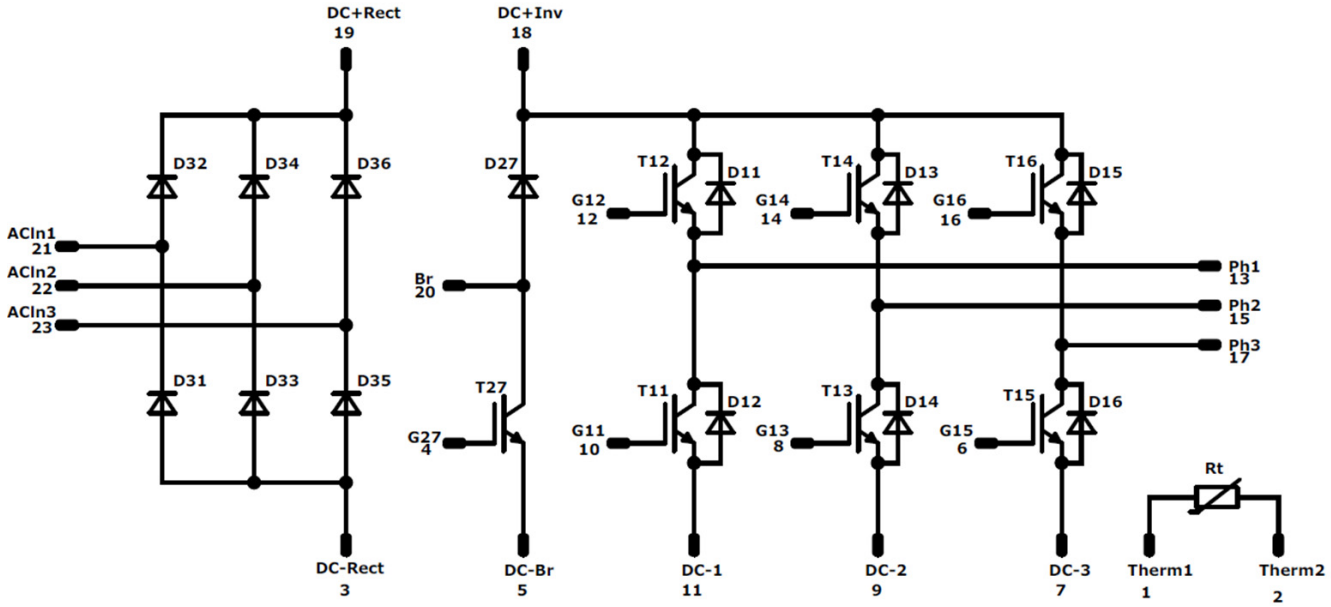
Outline

Pin table			
Pin	X	Y	Function
1	25,5	2,7	Therm1
2	25,5	0	Therm2
3	22,8	0	DC-Rect
4	20,1	0	G27
5	16,2	0	DC-Br
6	13,5	0	G15
7	10,8	0	DC-3
8	8,1	0	G13
9	5,4	0	DC-2
10	2,7	0	G11
11	0	0	DC-1
12	0	19,8	G12
13	0	22,5	Ph1
14	7,5	19,8	G14
15	7,5	22,5	Ph2
16	15	19,8	G16
17	15	22,5	Ph3
18	22,8	22,5	DC+Inv
19	25,5	22,5	DC+Rect
20	33,5	22,5	Br
21	33,5	15	ACIn1
22	33,5	7,5	ACIn2
23	33,5	0	ACIn3



Tolerance of pinpositions: ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	5 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	5 A	Inverter Diode	
T27	IGBT	1200 V	5 A	Brake Switch	
D27	FWD	1200 V	5 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	35 A	Rectifier Diode	
Rt	Thermistor			NTC	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for MiniSkiiP® 2 packages see vincotech.com website.

Package data
Package data for MiniSkiiP® 2 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-FZ12PMA005M701-P848A288-D1-14	12 Jul. 2018		